

Single-domain MoS₂: from single-layer growth to the formation of first bi-layer seeds

Moritz Ewert^{1,2,3}, Lars Buß^{1,2}, Francesca Genuzio⁴, Tevfik Onur Menteş⁴, Andrea Locatelli⁴, Jens Falta^{2,3}, and Jan Ingo Flege^{1,2,3}

¹*Applied Physics and Semiconductor Spectroscopy, Brandenburg University of Technology Cottbus-Senftenberg, Germany*

²*Institute of Solid State Physics, University of Bremen, Germany*

³*MAPEX Center for Materials and Processes, University of Bremen, Germany*

⁴*Elettra-Sincrotrone Trieste S.C.p.A., Basovizza, Trieste, Italy*

Email: mewert@b-tu.de

Single-layer molybdenum disulfide (MoS₂) is a heavily investigated transition metal dichalcogenide owing to its direct band gap, rendering it very promising for novel optical applications. Consequently, the electronic properties of single-layer MoS₂ have been studied experimentally with several surface science methods. A well-known, prototypical model system is MoS₂ on Au(111). Here, we present real-time observations of MoS₂ growth on Au(111) at elevated temperature using in-situ low-energy electron microscopy (LEEM). Our continuous growth method leads to the formation of micron-sized single-layer MoS₂ islands. Employing two distinctly different deposition rates and carefully selected growth temperatures, we are able to tune the growth mechanism of the MoS₂ islands from a balanced distribution of the two expected mirror domains towards a single-domain distribution. The single-domain character of these islands is confirmed by dark-field imaging and micro-diffraction (μ LEED), the former revealing a relative surface coverage of 90:10 of the mirror domains [1]. Intriguingly, selected-area angle-resolved photoelectron spectroscopy (μ ARPES) data of these mirror domains not only underline their three-fold symmetry, but also indicate the presence of MoS₂ bilayer regions. Using X-ray photoemission electron microscopy (XPEEM) and intensity-voltage (I(V)) LEEM, we identify the bilayer nucleation areas at nearly full surface coverage and propose a model pathway for their formation [2].

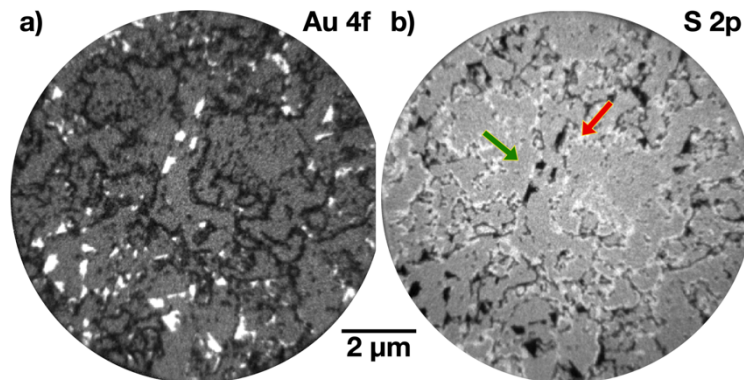


Figure 1. XPEEM data from Au4f_{7/2} (a) and S2p_{3/2} (b) core-level photoelectrons ($h\nu \approx 250$ eV).

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References

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